

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	Wafer Vendor
	5.0	Overall Thickness	546.00 +/- 16.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 100%
	8.0	Warp	<60.00μm	ADE to ASTM F534, 100%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	Any	Wafer Vendor
	13.0	Handle Thickness	500.00 +/- 15.00 μm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1 ~ 20 ohm-cm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and lasermark.	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle/ Device Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	45.00 +/- 1.00 μm	ADE Sigle Point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	25.0	Edge Removal Angle	45 +/- 15deg	Graranteed by process
	26.0	Edge Removal Depth in Handle	<100 um	Graranteed by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	phosphorus or Arsenic	Wafer Vendor
	29.0	Device Resistivity	< 0.003 ohm-cm	Wafer Vendor
	30.0	Voids	none	Bright Light, 100% (note 2)
	31.0	Scratches	<5 mm total length	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

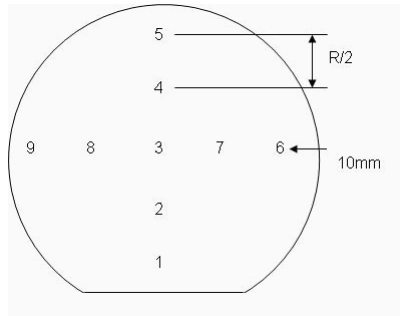
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information